

## Description

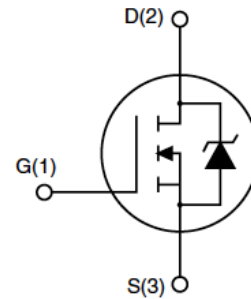
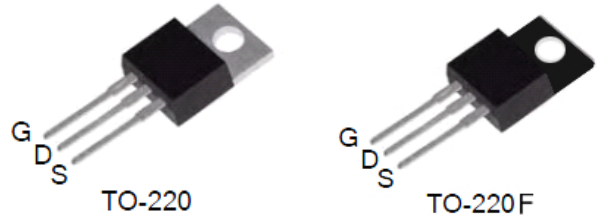
### Features

|           |                             |       |
|-----------|-----------------------------|-------|
| $V_{DSS}$ | $R_{DS(ON)}$<br>@ 10V (typ) | $I_D$ |
| 600V      | 0.94 $\Omega$               | 8.5A  |

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

### Application

- High frequency switching mode power supply
- Uninterruptible Power Supply (UPS)
- Electronic ballast



## Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise specified

| Symbol          | Parameter                                       |                           | Max.        |         | Units                     |
|-----------------|-------------------------------------------------|---------------------------|-------------|---------|---------------------------|
|                 |                                                 |                           | TO-220      | TO-220F |                           |
| $V_{DSS}$       | Drain-Source Voltage                            |                           | 600         |         | V                         |
| $V_{GSS}$       | Gate-Source Voltage                             |                           | $\pm 30$    |         | V                         |
| $I_D$           | Continuous Drain Current                        | $T_C = 25^\circ\text{C}$  | 8.5         | 8.5*    | A                         |
|                 |                                                 | $T_C = 100^\circ\text{C}$ | 5.32        | 5.32*   | A                         |
| $I_{DM}$        | Pulsed Drain Current <sup>note1</sup>           |                           | 34          | 34*     | A                         |
| $E_{AS}$        | Single Pulsed Avalanche Energy <sup>note2</sup> |                           | 180         |         | mJ                        |
| dv/dt           | Peak Diode Recovery Energy <sup>note3</sup>     |                           | 4.5         |         | V/ns                      |
| $P_D$           | Power Dissipation                               | $T_C = 25^\circ\text{C}$  | 130         | 50      | W                         |
|                 | Linear Derating Factor                          | $T_C > 25^\circ\text{C}$  | 1.04        | 0.4     | W/ $^\circ\text{C}$       |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case            |                           | 0.96        | 2.5     | $^\circ\text{C}/\text{W}$ |
| $T_J, T_{STG}$  | Operating and Storage Temperature Range         |                           | -55 to +150 |         | $^\circ\text{C}$          |

\*Drain current limited by maximum junction temperature

**Electrical Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise specified

| Symbol                                                 | Parameter                                                | Test Condition                                                          | Min. | Typ. | Max. | Units |
|--------------------------------------------------------|----------------------------------------------------------|-------------------------------------------------------------------------|------|------|------|-------|
| Off Characteristic                                     |                                                          |                                                                         |      |      |      |       |
| V <sub>(BR)DSS</sub>                                   | Drain-Source Breakdown Voltage                           | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA                            | 600  | -    | -    | V     |
| ΔV <sub>(BR)DSS</sub><br>/ΔT <sub>J</sub>              | Breakdown Voltage Temperature<br>Coefficient             | Reference to 25℃,<br>I <sub>D</sub> = 250μA                             | -    | 0.65 | -    | V/℃   |
| I <sub>DSS</sub>                                       | Zero Gate Voltage Drain Current                          | V <sub>DS</sub> = 600V, V <sub>GS</sub> = 0V                            | -    | -    | 1    | μA    |
|                                                        |                                                          | V <sub>DS</sub> = 480V, T <sub>C</sub> = 125℃                           | -    | -    | 10   | μA    |
| I <sub>GSS</sub>                                       | Gate to Body Leakage Current                             | V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±30V                            | -    | -    | ±100 | nA    |
| On Characteristics                                     |                                                          |                                                                         |      |      |      |       |
| V <sub>GS(th)</sub>                                    | Gate Threshold Voltage <sup>note4</sup>                  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA              | 2    | -    | 4    | V     |
| R <sub>DS(on)</sub>                                    | Static Drain-Source On-Resistance                        | V <sub>GS</sub> =10V, I <sub>D</sub> = 4.25A                            | -    | 0.94 | 1.1  | Ω     |
| g <sub>FS</sub>                                        | Forward Transconductance                                 | V <sub>DS</sub> =30V, I <sub>D</sub> = 4.25A                            | -    | 6.8  | -    | S     |
| Dynamic Characteristics                                |                                                          |                                                                         |      |      |      |       |
| C <sub>iss</sub>                                       | Input Capacitance                                        | V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz              | -    | 1230 | -    | pF    |
| C <sub>oss</sub>                                       | Output Capacitance                                       |                                                                         | -    | 98.2 | -    | pF    |
| C <sub>rss</sub>                                       | Reverse Transfer Capacitance                             |                                                                         | -    | 5.29 | -    | pF    |
| Q <sub>g</sub>                                         | Total Gate Charge                                        | V <sub>DD</sub> = 480V, I <sub>D</sub> = 8.5A,<br>V <sub>GS</sub> = 10V | -    | 27.7 | -    | nC    |
| Q <sub>gs</sub>                                        | Gate-Source Charge                                       |                                                                         | -    | 4.75 | -    | nC    |
| Q <sub>gd</sub>                                        | Gate-Drain(“Miller”) Charge                              |                                                                         | -    | 9.81 | -    | nC    |
| Switching Characteristics                              |                                                          |                                                                         |      |      |      |       |
| t <sub>d(on)</sub>                                     | Turn-On Delay Time                                       | V <sub>DD</sub> = 300V, I <sub>D</sub> = 8.5A,<br>RG = 10Ω, VGS = 10V   | -    | 23   | -    | ns    |
| t <sub>r</sub>                                         | Turn-On Rise Time                                        |                                                                         | -    | 27.3 | -    | ns    |
| t <sub>d(off)</sub>                                    | Turn-Off Delay Time                                      |                                                                         | -    | 73.3 | -    | ns    |
| t <sub>f</sub>                                         | Turn-Off Fall Time                                       |                                                                         | -    | 28.5 | -    | ns    |
| Drain-Source Diode Characteristics and Maximum Ratings |                                                          |                                                                         |      |      |      |       |
| I <sub>S</sub>                                         | Maximum Continuous Drain to Source Diode Forward Current |                                                                         | -    | -    | 8.5  | A     |
| I <sub>SM</sub>                                        | Maximum Pulsed Drain to Source Diode Forward Current     |                                                                         | -    | -    | 34   | A     |
| V <sub>SD</sub>                                        | Drain to Source Diode Forward Voltage                    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 8.5A                             | -    | -    | 1.4  | V     |
| t <sub>rr</sub>                                        | Reverse Recovery Time                                    | V <sub>GS</sub> = 0V, I <sub>F</sub> = 8.5A,                            | -    | 452  | -    | ns    |
| Q <sub>rr</sub>                                        | Reverse Recovery Charge                                  | di/dt =100A/μs                                                          | -    | 3.6  | -    | uC    |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 10\text{mH}$ ,  $I_{AS} = 6A$ ,  $V_{DD} = 50V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}\text{C}$
3.  $I_{SD} \leq 8.5A$ ,  $di/dt \leq 200A/\mu s$ ,  $V_{DD} \leq B_{VDSS}$ , Starting  $T_J = 25^{\circ}\text{C}$
4. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

## Typical Performance Characteristics

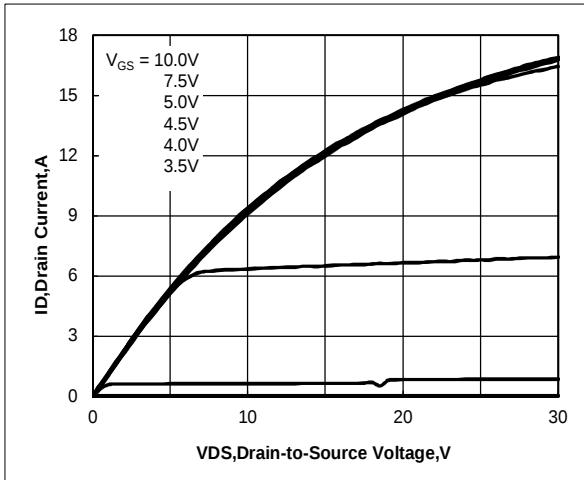


Figure 1. Output Characteristics

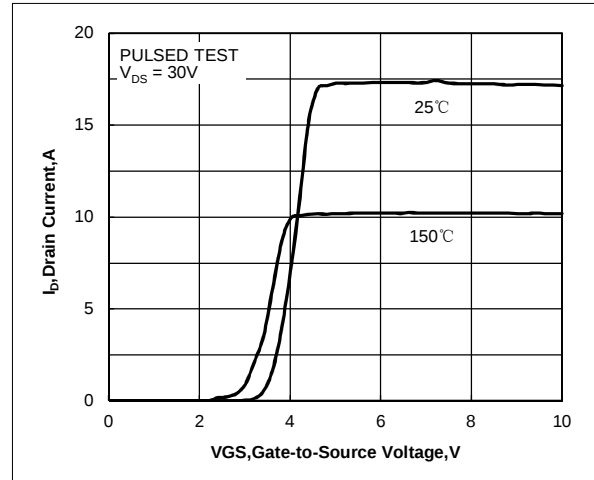


Figure 2. Transfer Characteristics

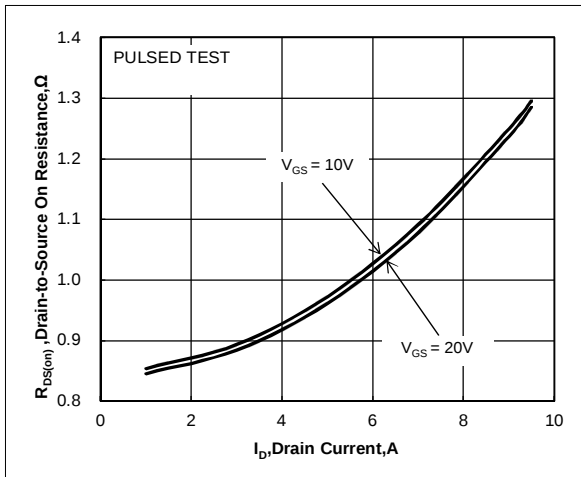


Figure 3. Drain-to-Source On Resistance vs. Drain Current and Gate Voltage

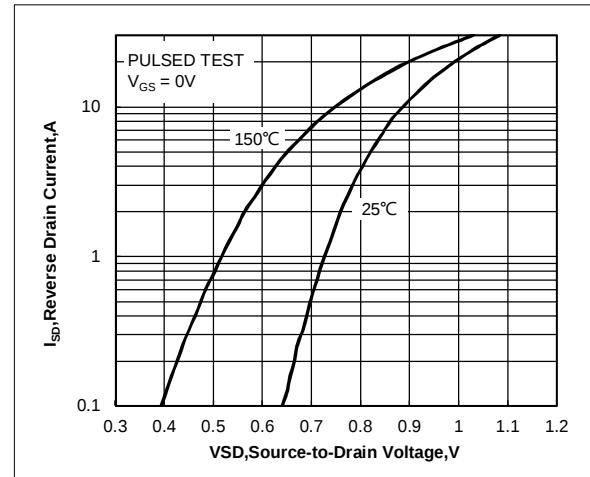


Figure 4. Body Diode Forward Voltage vs. Source Current and Temperature

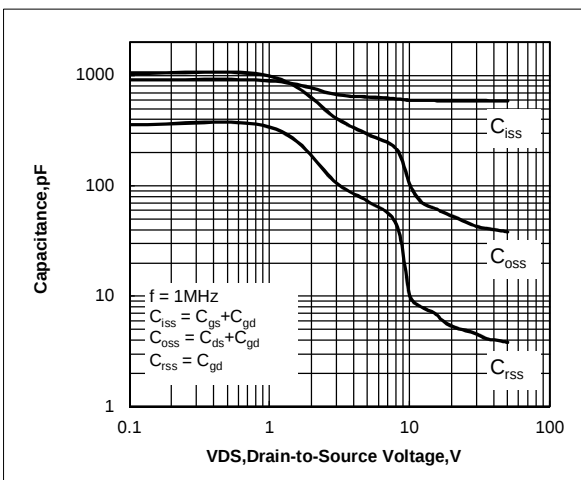


Figure 5. Capacitance Characteristics

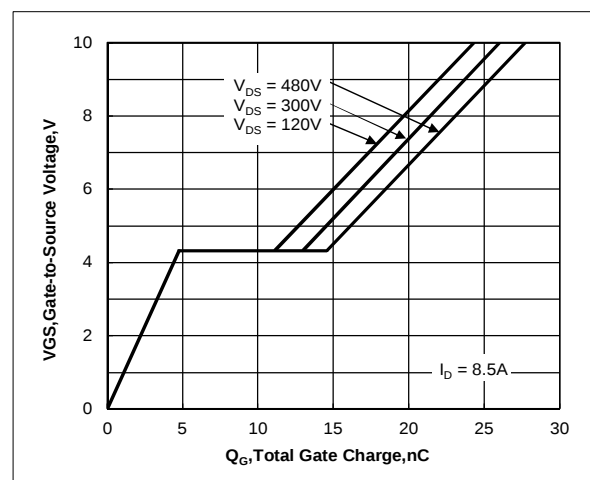


Figure 6. Gate Charge Characteristics

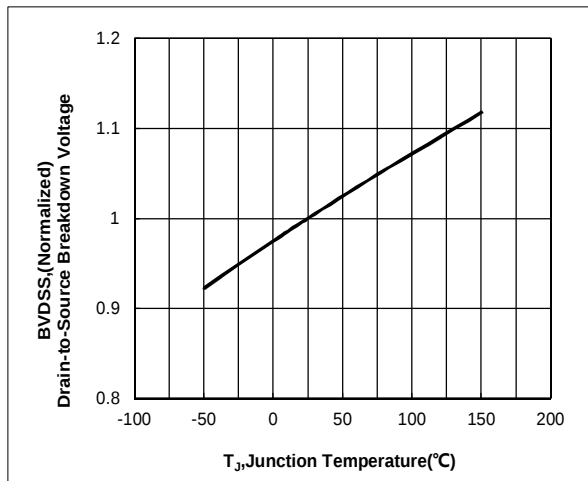


Figure 7. Normalized Breakdown Voltage vs. Junction Temperature

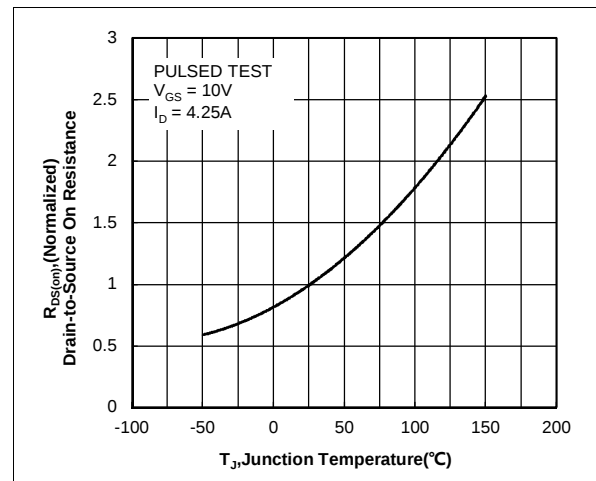


Figure 8. Normalized On Resistance vs. Junction Temperature

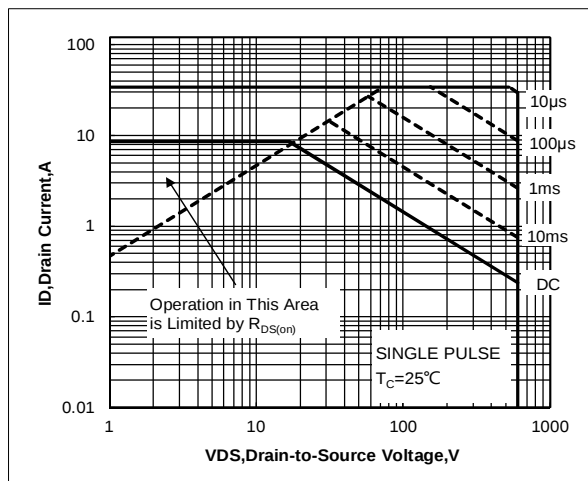


Figure 9. Maximum Safe Operating Area for RP8N60A

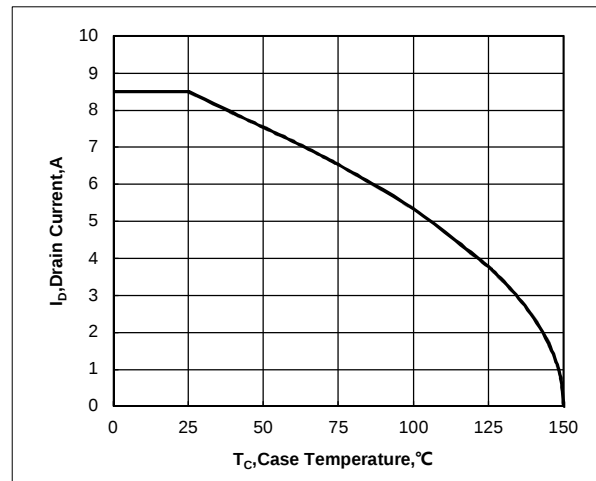


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

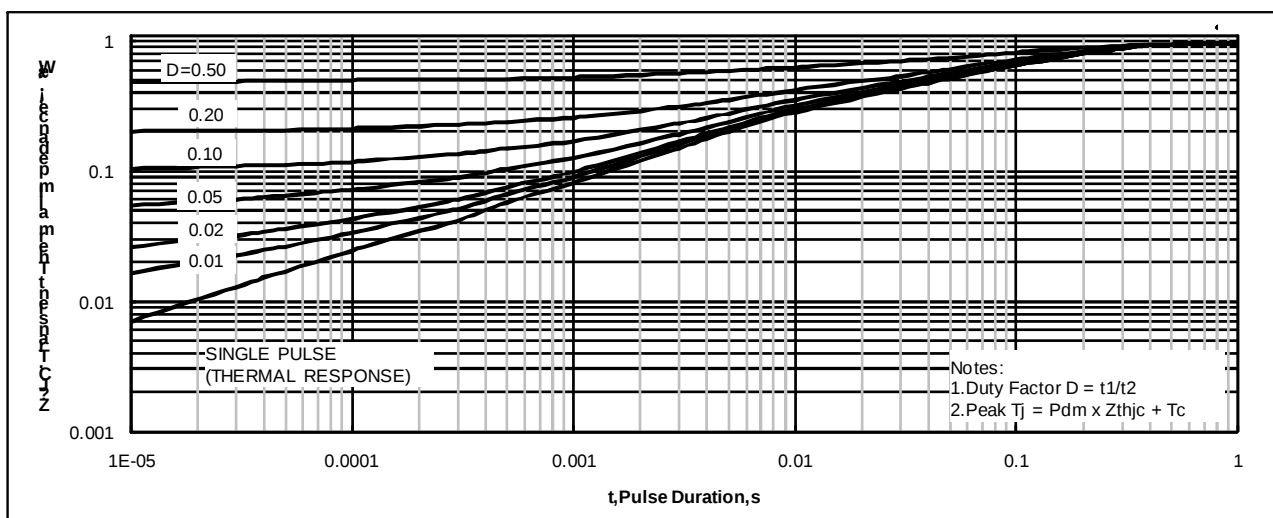


Figure 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case for RP8N60A

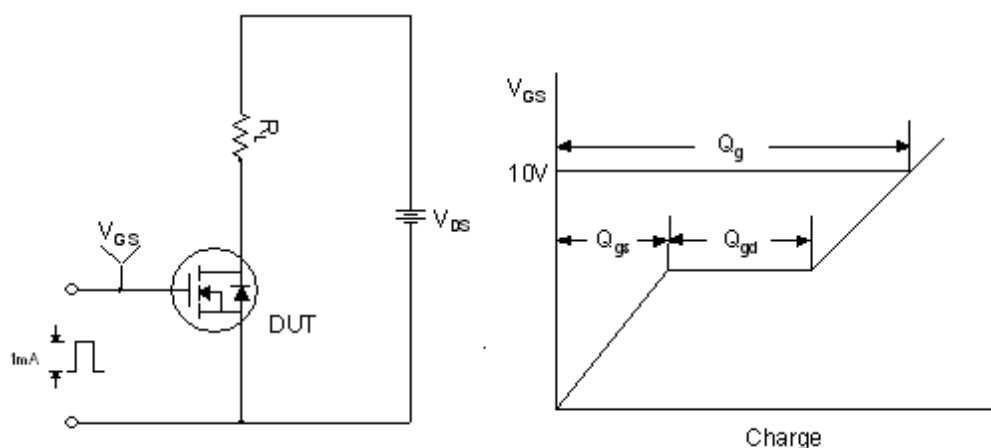


Figure 12. Gate Charge Test Circuit & Waveform

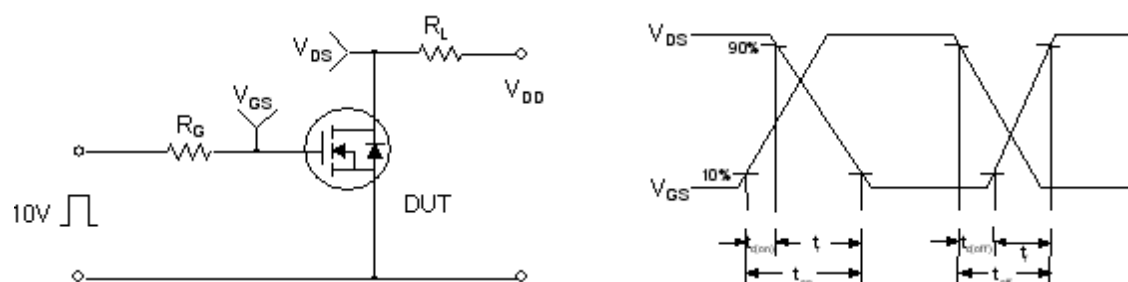


Figure 13. Resistive Switching Test Circuit & Waveforms

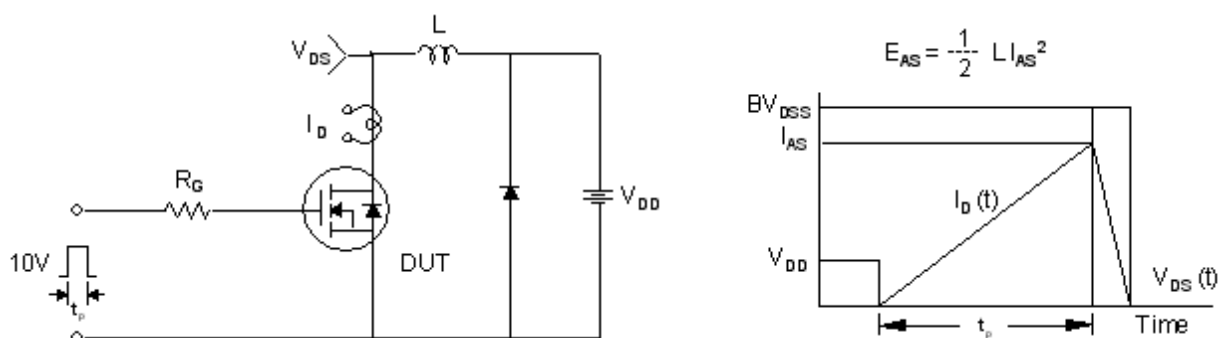


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

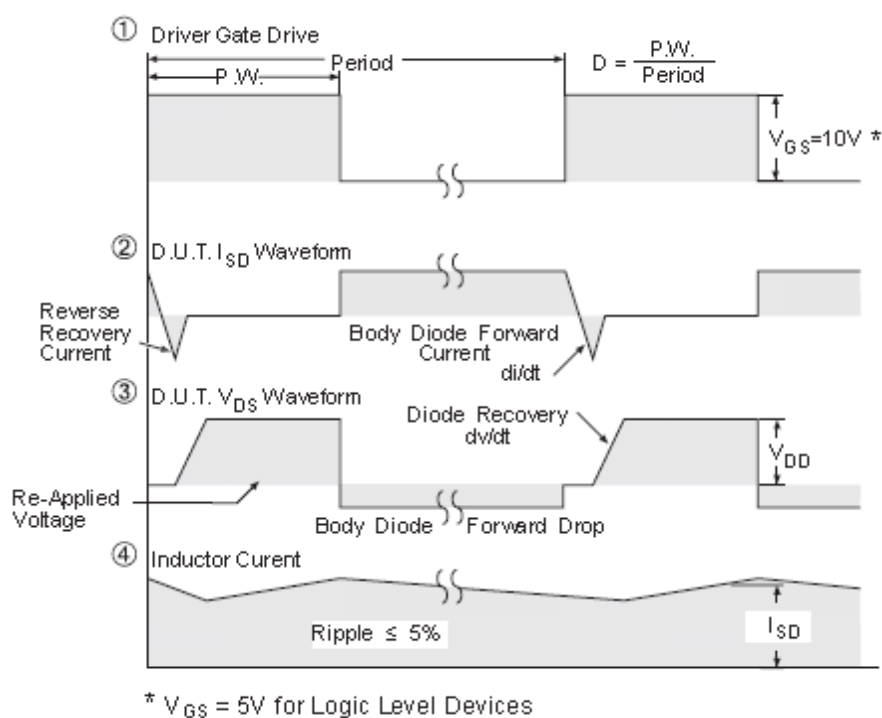
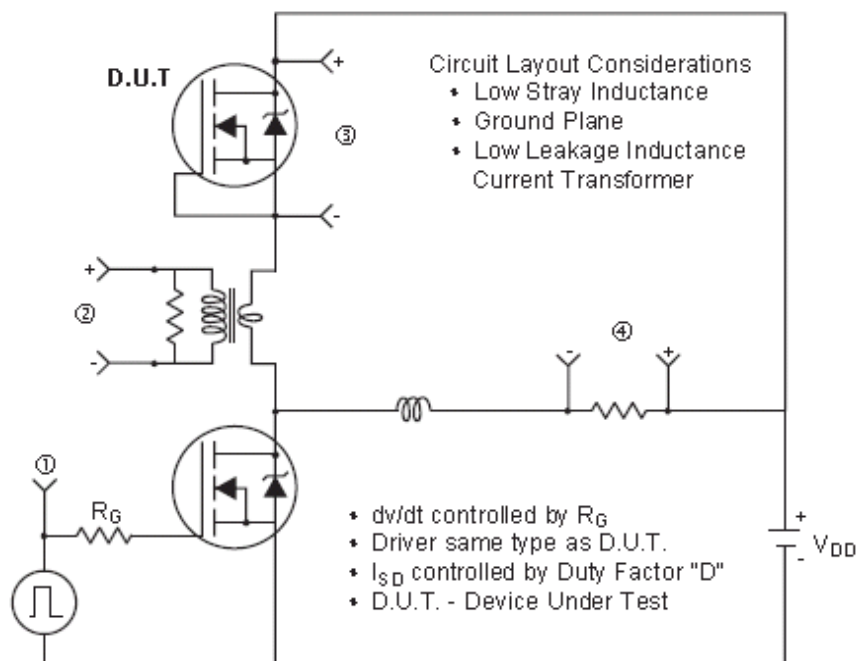


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms (For N-channel)